









SN74HCT245-EP JAJSQP7 - JULY 2023

SN74AHCT245-EP エンハンスド製品、5V、3 ステート出力、オクタル バストランシ ーバ

1 特長

- 入力は TTL 電圧互換
- JESD 17 準拠で 250mA 超のラッチアップ性能
- 防衛、航空宇宙、医療アプリケーションをサポー **ト**:
 - 管理されたベースライン
 - 単一のアセンブリおよびテスト施設
 - 単一の製造施設
 - 長い製品ライフ・サイクル
 - 製品のトレーサビリティ

2 アプリケーション

- デジタル信号のイネーブルまたはディセーブル
- コントローラ・リセット時の信号保持
- スイッチのデバウンス

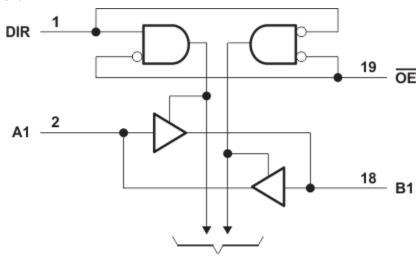
3 概要

SN74AHCT245-EP オクタル・バス・トランシーバ は、データ・バス間の非同期双方向通信用に設計され ています。これらの部品は、4.5V~5.5V で動作しま す。

パッケージ情報

部品番号	パッケージ ⁽¹⁾	パッケージ・サイ ズ ⁽²⁾	本体サイズ (公称)
SN74AHCT245- EP	PW (TSSOP、 20)	6.5mm × 6.4mm	6.5mm × 4.4mm

- 利用可能なすべてのパッケージについては、データシートの (1) 末尾にある注文情報を参照してください。
- パッケージ・サイズ (長さ×幅) は公称値であり、該当する場 合はピンも含まれます。
- 本体サイズ (長さ×幅) は公称値であり、ピンは含まれませ



To Seven Other Channels 概略回路図



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4 Revision History

DATE	REVISION	NOTES
July 2023	*	Initial Release



5 Pin Configuration and Functions

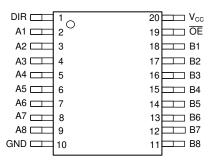


図 5-1. SN74AHCT245-EP: PW Package, 20-Pin TSSOP (Top View)

表 5-1. Pin Functions

PIN		TYPE(1)	DESCRIPTION
NAME	NO.	- ITPE("/	DESCRIPTION
DIR	1	ı	Direction Pin
A1	2	I/O	A1 Input/Output
A2	3	I/O	A2 Input/Output
A3	4	I/O	A3 Input/Output
A4	5	I/O	A4 Input/Output
A5	6	I/O	A5 Input/Output
A6	7	I/O	A6 Input/Output
A7	8	I/O	A7 Input/Output
A8	9	I/O	A8 Input/Output
GND	10	G	Ground Pin
B8	11	I/O	B8 Input/Output
B7	12	I/O	B7 Input/Output
B6	13	I/O	B6 Input/Output
B5	14	I/O	B5 Input/Output
B4	15	I/O	B4 Input/Output
B3	16	I/O	B3 Input/Output
B2	17	I/O	B2 Input/Output
B1	18	I/O	B1 Input/Output
ŌĒ	19	I	Output Enable
VCC	20	Р	Power Pin

⁽¹⁾ I = Input, O = Output, P= Positive Supply, G = Ground



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			·		MIN	MAX	UNIT
V _{CC}	Supply voltage range	Supply voltage range				7	V
VI	Input voltage range ⁽²⁾ Control inputs			Control inputs	-0.5	7	V
Vo	Output voltage range ⁽²⁾				-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		Control inputs		-20	mA
I _{OK}	Output clamp current	$V_O < 0$ or $V_O > 1$	V _{CC}			±20	mA
Io	Continuous output current	$V_O = 0$ to V_{CC}				±25	mA
	Continuous current through V _{CC} or G	iND)			±75	mA
T _{stg}	Storage temperature				-65	150	°C

⁽¹⁾ Operation outside the Absolute Maximum Rating may cause permanent device damage. Absolute Maximum Rating do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Condition. If used outside the Recommended Operating Condition but within the Absolute Maximum Rating, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

6.2 ESD Ratings

			MIN	MAX	UNIT
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾		±2000	\/
V _(ESD)	Liectiostatic discharge	Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾		±1000	v

JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

		SN74AHCT2	UNIT	
		MIN	UNIT	
V _{CC}	Supply voltage	4.5	5.5	V
V _{IH}	High-level input voltage	2		V
V _{IL}	Low-level Input voltage		0.8	V
VI	Input voltage	0	5.5	V
Vo	Output voltage	0	Vcc	V
I _{OH}	High-level output current		-8	mA
I _{OL}	Low-level output current		8	mA
Δt/Δν	Input Transition rise and fall rate		20	ns/V
T _A	Operating free-air temperature	– 55	125	°C

All unused inputs of the device must be held at V_{CC} or GND for proper device operation. Refer to the TI application report, *Implications* of Slow or Floating CMOS Inputs, literature number SCBA004.

⁽²⁾ The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.4 Thermal Information

		SN74AHCT245-EP	
	THERMAL METRIC ⁽¹⁾	PW	UNIT
		20 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	102.8	
R _{θJC(top)}	Junction-to-case (top) thermal resistance	36.8	
R _{θJB}	Junction-to-board thermal resistance	53.8	°C/W
Ψлт	Junction-to-top characterization parameter	2.5	C/VV
ΨЈВ	Junction-to-board characterization parameter	53.3	
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	n/a	

⁽¹⁾ For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

DAI	PARAMETER TEST CONDITIONS V.		TA = 25°C				-55°C to 125°	UNIT		
PAI	KAIVIETEK	TEST CONDITIONS	V _{CC}	MIN	TYP	MAX	MIN	MAX	UNII	
V _{OH}		I _{OH} = -50 μA	4.5 V	4.4	4.5		4.4		V	
VOH		I _{OH} = -8 mA	4.5 V	3.94			3.7		V	
V _{OL}		I _{OL} = 50 μA	4.5 V			0.1		0.1	1 V	
VOL		I _{OH} = 8 mA	4.5 V			0.36		0.44	V	
I _I	OE or DIR	V _I = 5.5 V or GND	0 to 5.5 V			±0.1		±1	μΑ	
I _{OZ}	A or B inputs ⁽¹⁾	V _O = V _{CC} or GND	5.5 V			±.25		±2.5	μA	
I _{CC}		$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			4		40	μΑ	
ΔI _{CC} (2)		One input at 3.4 V, Other inputs at V _{CC} or GND	5.5 V			1.35		1.5	mA	
C _i	OE or DIR	V _I = V _{CC} or GND	5 V		2.5	10			pF	
C _{io}	A or B inputs	V _I = V _{CC} or GND	5 V		4				pF	

⁽¹⁾ For I/O ports, the parameter I_{OZ} includes the input leakage current.

⁽²⁾ This is the increase in supply current for each input at one of the specified TTL voltage levels, rather than 0 V or V_{CC}.



6.6 Switching Characteristics

over recommended operating free-air temperature range, V_{CC} = 5 V \pm 0.5 V (unless otherwise noted)

PARAMETER	FROM	то	LOAD	T _A = 25°	C	-55°C to 1	25°C	UNIT
PARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	TYP	MAX	MIN	MAX	UNII
t _{PLH}	A or B	B or A	C _L = 15 pF	4.5	7.7	1	10	ns
t _{PHL}	AOID	BOIA	OL = 13 pi	4.5	7.7	1	10	115
t _{PZH}	 OE	A or B	C _L = 15 pF	8.9	13.8	1	16	ns
t _{PZL}	OE OE	AOIB	OL = 13 pi	8.9	13.8	1	16	115
t _{PHZ}	 OE	A or B	C _L = 15 pF	9.2	14.4	1	16.5	ns
t _{PLZ}	OL	AOIB	OL = 13 pi	9.2	14.4	1	16.5	115
t _{PLH}	A or B	B or A	C _L = 50 pF	5.3	8.7	1	11	ns
t _{PHL}	AOID	BOIA	О[– 30 рі	5.3	8.7	1	11	115
t _{PZH}	 OE	A or B	9.7	14.8	1	17	ns	
t _{PZL}	OL	AOIB	О[– 30 рі	9.7	14.8	1	17	115
t _{PHZ}	ŌĒ	A or B	C _L = 50 pF	10	15.4	1	17.5	ns
t _{PLZ}	OE	AUIB	CL = 50 pr	10	15.4	1	17.5	115
t _{sk(o)}			C _L = 50 pF		1			ns

6.7 Noise Characteristics

 $V_{CC} = 5 \text{ V}, C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C}^{(1)}$

	PARAMETER	SN74A	HCT245	5-EP	UNIT
	PARAINE I ER	MIN		UNII	
V _{OH(V)}	Quiet output, minimum dynamic V _{OH}		4		V
V _{IH(D)}	High-level dynamic input voltage	2			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.8	V

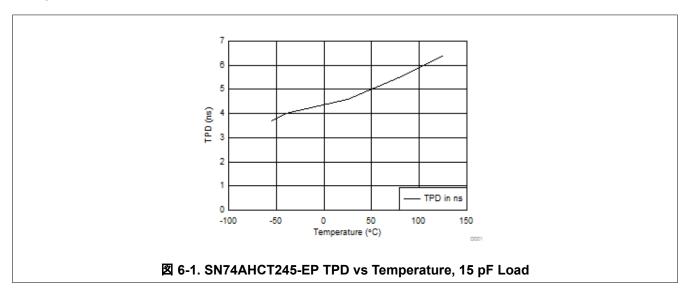
⁽¹⁾ Characteristics are for surface-mount packages only.

6.8 Operating Characteristics

 $V_{CC} = 5 \text{ V}, T_A = 25^{\circ}\text{C}$

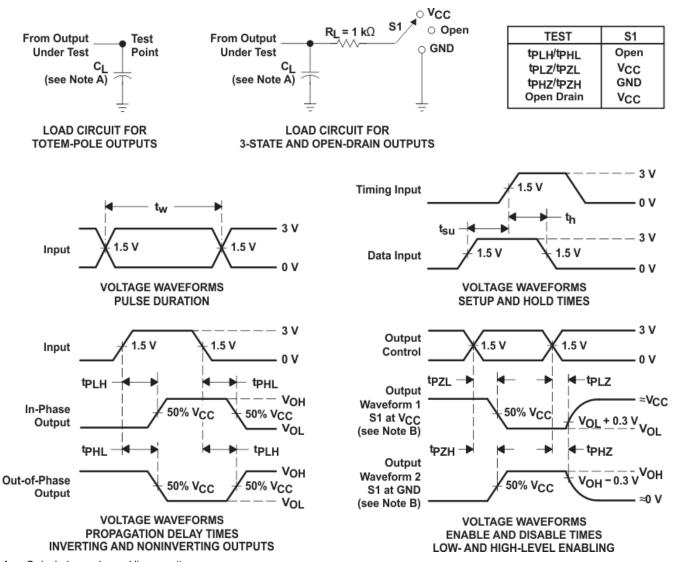
PARAMETER		TEST CO	NDITIONS	TYP	UNIT
C _{pd}	Power dissipation capacitance	No load,	f = 1 MHz	13	pF

6.9 Typical Characteristics





7 Parameter Measurement Information



- A. C_L includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.
 Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, $Z_O = 50 \Omega$, $t_r \leq 3 \text{ ns}$.
- D. The outputs are measured one at a time with one input transition per measurement.
- E. All parameters and waveforms are not applicable to all devices.

図 7-1. Load Circuit and Voltage Waveforms

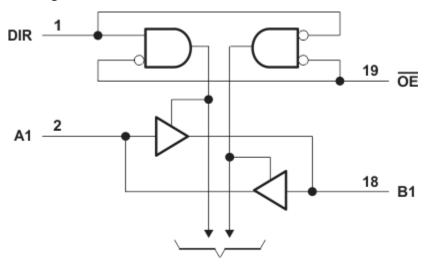
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8 Detailed Description

8.1 Overview

The SNx7ACHT245 octal bus transceivers are designed for asynchronous two-way communication between data buses. The control-function implementation minimizes external timing requirements. The SN74AHCT245-EP devices allow data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable (OE) input can be used to disable the device so that the buses effectively are isolated. For the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

8.2 Functional Block Diagram



To Seven Other Channels

図 8-1. Logic Diagram (Positive Logic)

8.3 Feature Description

- V_{CC} is optimized at 5 V
- Allows up voltage translation from 3.3 V to 5 V
 - Inputs accept V_{IH} levels of 2 V
- Slow edge rates minimize output ringing

8.4 Device Functional Modes

表 8-1. Function Table (Each Transceiver)

INP	UTS	OPERATION			
ŌĒ	DIR				
L	L	B data to A bus			
L	Н	A data to B bus			
Н	Χ	Isolation			



9 Application and Implementation



Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The SN74AHCT245-EP can be used to drive signals over relatively long traces or transmission lines. To reduce ringing caused by impedance mismatches between the driver, transmission line, and receiver, a series damping resistor placed in series with the transmitter's output can be used. The figure in the *Application Curve* section shows the received signal with three separate resistor values. Just a small amount of resistance can make a significant impact on signal integrity in this type of application.

9.2 Typical Application

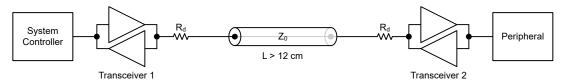


図 9-1. Application Block Diagram

9.3 Design Requirements

9.3.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics*.

The positive voltage supply must be capable of sourcing current equal to the maximum static supply current, I_{CC}, listed in the *Electrical Characteristics* and any transient current required for switching.



The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74AHCT245-EP plus the maximum supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current as can be sunk into its ground connection. Be sure not to exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74AHCT245-EP can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

The SN74AHCT245-EP can drive a load with total resistance described by $R_L \ge V_O$ / I_O , with the output voltage and current defined in the *Electrical Characteristics* table with V_{OL} . When outputting in the high state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in CMOS Power Consumption and Cpd Calculation.

Thermal increase can be calculated using the information provided in Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices.

注意

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.3.2 Input Considerations

Input signals must cross to be considered a logic LOW, and to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74AHCT245-EP, as specified in the *Electrical Characteristics*, and the desired input transition rate. A 10-k Ω resistor value is often used due to these factors.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.3.3 Output Considerations

The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to Feature Description section for additional information regarding the outputs for this device.

9.3.4 Detailed Design Procedure

- Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
- Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit; it will, however, ensure
 optimal performance. This can be accomplished by providing short, appropriately sized traces from the
 SN74AHCT245-EP to one or more of the receiving devices.
- 3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)}) \Omega$. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in M Ω ; much larger than the minimum calculated previously.
- 4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, *CMOS Power Consumption and Cpd Calculation*.

9.4 Application Curves

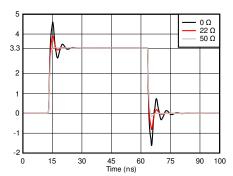


图 9-2. Simulated Signal Integrity at the Receiver With Different Damping Resistor (R_d) Values

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. The 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in the following layout example.

11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

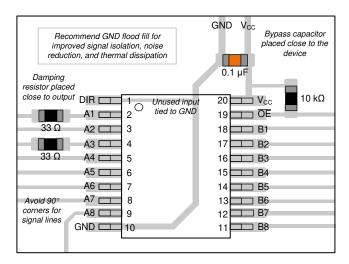


図 11-1. Example Layout for the SN74AHCT245-EP in PW



12 Device and Documentation Support

12.1 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.com のデバイス製品フォルダを開いてください。「更新の通知を受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

12.2 サポート・リソース

TI E2E™ サポート・ フォーラムは、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計で必要な支援を迅速に得ることができます。

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12.3 Trademarks

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12.4 静電気放電に関する注意事項



この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

12.5 用語集

テキサス・インスツルメンツ用語集 この用語集には、用語や略語の一覧および定義が記載されています。

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74AHCT245MPWREP	ACTIVE	TSSOP	PW	20	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HB245EP	Samples
V62/23618-01XE	ACTIVE	TSSOP	PW	20	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		HB245EP	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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OTHER QUALIFIED VERSIONS OF SN74AHCT245-EP:

● Catalog : SN74AHCT245

• Automotive : SN74AHCT245-Q1

• Military : SN54AHCT245

NOTE: Qualified Version Definitions:

• Catalog - TI's standard catalog product

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

• Military - QML certified for Military and Defense Applications



SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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